General Description

The silicon carbide power MOSFET utilizes Oriental-Semi's advanced technology to achieve low on-resistance, low gate charge, low Qrr and excellent thermal performance by exploiting innovative properties of wide bandgap materials. It is engineered to minimize conduction loss and provide superior switching performance almost independent of temperature.
The silicon carbide power MOSFET provides high reliability and extremely high efficiency. It is targeted to improve application performance in frequency, energy efficiency, reliability, system size and weight reduction.

Features

- High blocking voltage with low on-resistance
- High-speed switching with low capacitances
- IGBT-compatible driving voltage (15V for turn-on)
- Fast intrinsic diode with low reverse recovery (Qrr)
- Temperature independent turn-off switching losses
- Halogen free, RoHS compliant
- AEC-Q101 Qualified

Applications

- Solar inverters
- On-board charger/PFC
- EV motor drive
- High voltage DC/DC converters
- Switch mode power supplies

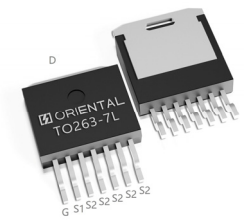
Key Performance Parameters

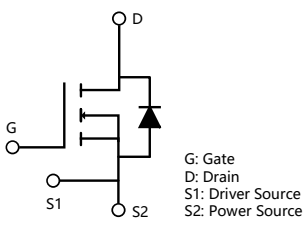
Parameter	Value	Unit
V_{DS}	1200	V
$I_{D,\ pulse}$	100	A
$R_{DS(ON),\ typ}$ @ V_{GS}=18V	60	mΩ
Q_g	47	nC

Marking Information

Product Name	Package	Marking
OSQ120R060K7T2AF	TO263-7L	OSQ120R060K7T2A

Package & Pin Information





Absolute Maximum Ratings at T_j=25°C unless otherwise noted

Parameter	Symbol	Value	Unit
Drain-source voltage	V_{DS}	1200	V
Gate-source voltage (max static)	V_{GS}	-8/+22	V
Gate-source voltage (recommended operating values)	V_{GS}	-4/+18	V
Continuous drain current[1], T_C=25 °C	I_D	39	A
Continuous drain current[1], T_C=100 °C		27	
Pulsed drain current[2]	$I_{D,\ pulse}$	100	A
Power dissipation[3], T_C=25 °C	P_D	165	W
Operation and storage temperature	T_{stg}, T_j	-55 to 175	°C

Thermal Characteristics

Parameter	Symbol	Min.	Typ.	Max.	Unit
Thermal resistance, junction-case	$R_{\theta JC}$		0.70	0.91	°C/W
Thermal resistance, junction-ambient	$R_{\theta JA}$			62	°C/W

Electrical Characteristics at T_j=25°C unless otherwise specified

Parameter	Symbol	Min.	Typ.	Max.	Unit	Test condition
Drain-source breakdown voltage	BV_{DSS}	1200			V	V_{GS}=0 V, I_D=100 μA
Gate threshold voltage	$V_{GS(th)}$	2.3	2.8	3.6	V	V_{DS}=V_{GS}, I_D=5 mA
Drain-source on-state resistance	$R_{DS(ON)}$		60	75	mΩ	V_{GS}=18 V, I_D=20 A
			110			V_{GS}=18 V, I_D=20 A, T_j=175 °C
			74	100	mΩ	V_{GS}=15 V, I_D=20 A
			117			V_{GS}=15 V, I_D=20 A, T_j=175 °C
Transconductance	g_{fs}		16		S	V_{DS} = 20 V, I_D =20 A
Gate-source leakage current	I_{GSS}			±100	nA	V_{GS}=-8~22 V
Drain-source leakage current	I_{DSS}			100	μA	V_{DS}=1200 V, V_{GS}=0 V
				500	μA	V_{DS}=1200 V, V_{GS}=0 V, T_j=175 °C
Gate resistance	R_G		2.3		Ω	f=1 MHz, Open drain, V_{AC}=25 mV

Dynamic Characteristics

Parameter	Symbol	Min.	Typ.	Max.	Unit	Test condition
Input capacitance	C_{iss}		1149		pF	V_{GS}=0 V, V_{DS}=800 V, f=1 MHz, V_{AC}=25 mV
Output capacitance	C_{oss}		55		pF	
Reverse transfer capacitance	C_{rss}		2		pF	
C_{oss} stored energy	E_{OSS}		23		μJ	
Turn-on delay time	$t_{d(on)}$		10.8		ns	V_{GS}=-4/18 V, V_{DS}=800 V, R_G=5 Ω, I_D=15 A, L=120 μH, T_j=25 °C
Rise time	t_r		8.2		ns	
Turn-off delay time	$t_{d(off)}$		18		ns	
Fall time	t_f		8.7		ns	
Turn-on switching energy	E_{on}		108		μJ	
Turn-off switching energy	E_{off}		22		μJ	
Turn-on switching energy	E_{on}		99		μJ	V_{GS}=-4/18 V, V_{DS}=800 V, R_G=5 Ω, I_D=15 A, L=120 μH, T_j=175 °C
Turn-off switching energy	E_{off}		21		μJ	

Gate Charge Characteristics

Parameter	Symbol	Min.	Typ.	Max.	Unit	Test condition
Total gate charge	Q_g		47		nC	V_{GS}=-4/18 V, V_{DS}=800 V, I_D=15 A
Gate-source charge	Q_{gs}		15.7		nC	
Gate-drain charge	Q_{gd}		9.7		nC	

Body Diode Characteristics

Parameter	Symbol	Min.	Typ.	Max.	Unit	Test condition
Diode forward voltage	V_{SD}		4.5		V	I_S=15 A, V_{GS}=-4 V, T_j=25 °C
			4.0		V	I_S=15 A, V_{GS}=-4 V, T_j=175 °C
Continuous diode forward current	Is		39		A	V_{GS}=-4 V, T_j=25 °C
Reverse recovery time	t_{rr}		13.6		ns	V_{GS}=-4 V, V_R=800 V, I_S=15 A, di/dt=3000 A/μs, T_j=25 °C
Reverse recovery charge	Q_{rr}		102		nC	
Peak reverse recovery current	I_{rrm}		12.7		A	
Reverse recovery time	t_{rr}		46.5		ns	V_{GS}=-4 V, V_R=800 V, I_S=15 A, di/dt=1000 A/μs, T_j=175 °C
Reverse recovery charge	Q_{rr}		181		nC	
Peak reverse recovery current	I_{rrm}		5.8		A	

Note

1) Calculated continuous current based on maximum allowable junction temperature.
2) Repetitive rating; pulse width limited by max. junction temperature.
3) Pd is based on max. junction temperature, using junction-case thermal resistance.

Electrical Characteristics Diagrams

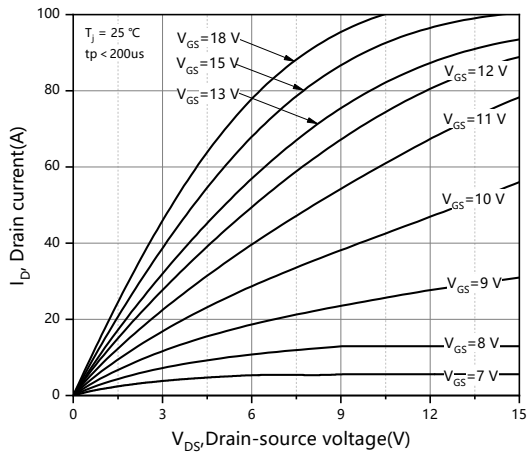


Figure 1.Output characteristics T_j=25℃

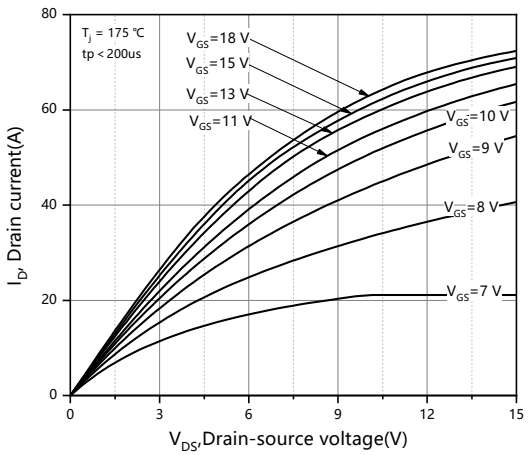


Figure 2.Output characteristics T_j=175℃

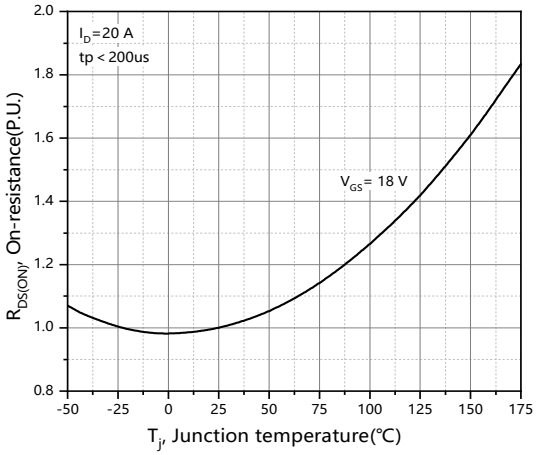


Figure 3. Normalized on-resistance vs. temperature

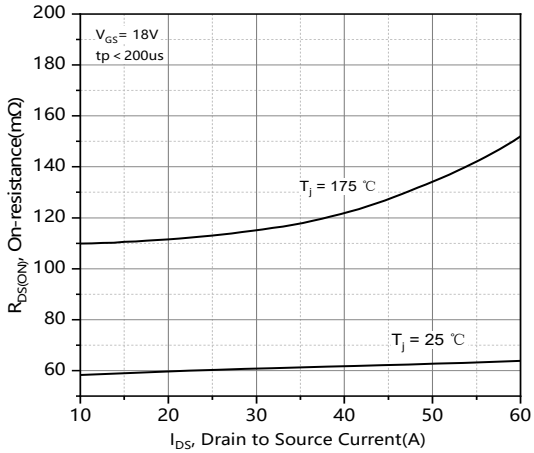


Figure 4. On-resistance vs. drain current for various temperatures

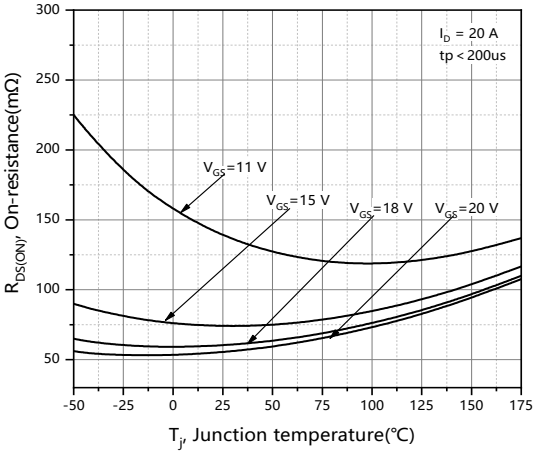


Figure 5. On-resistance vs. temperature for various gate voltage

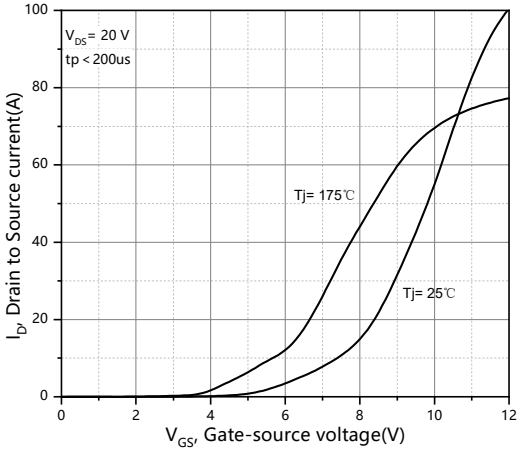


Figure 6. Transfer characteristic for various junction temperatures

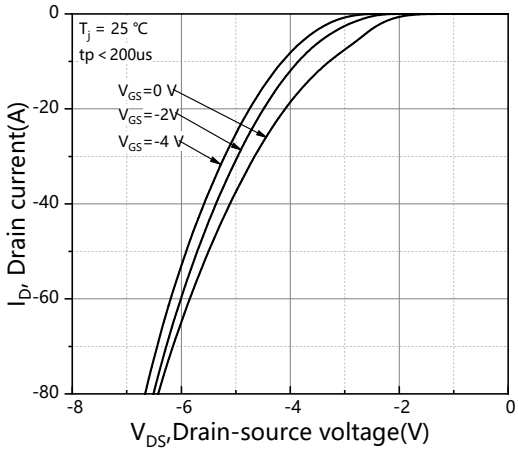


Figure 7. Body diode characteristic at T_j = 25 ºC

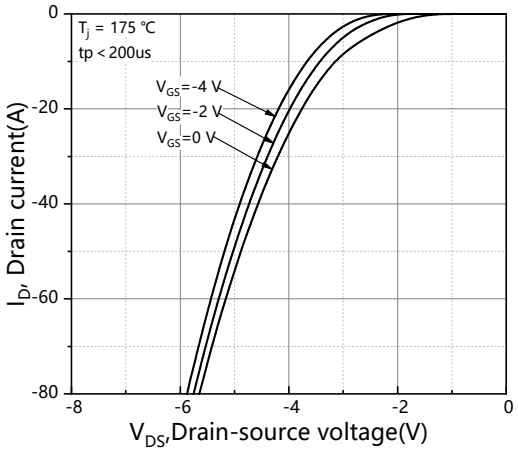


Figure 8. Body diode characteristic at T_j = 175ºC

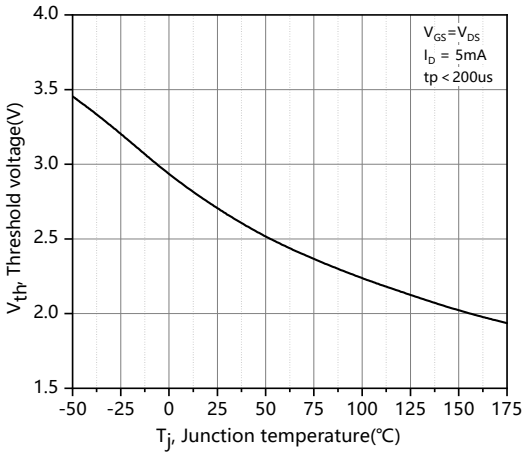


Figure 9. Threshold voltage vs. temperature

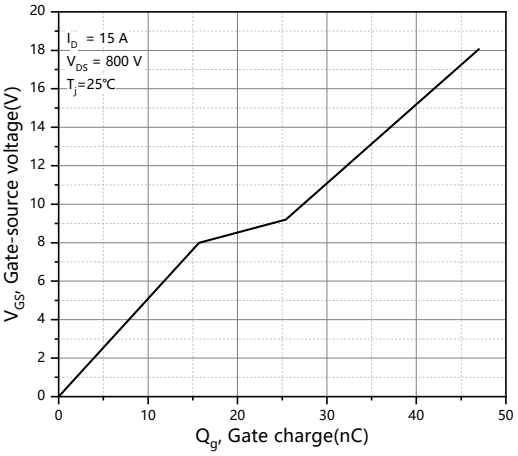


Figure 10. Gate charge characteristic

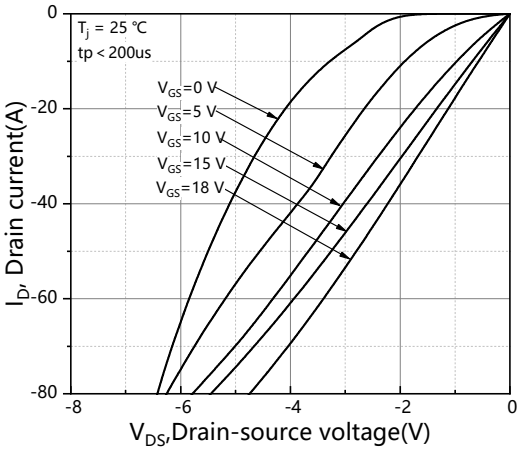


Figure 11. 3rd quadrant characteristic at T_j = 25 ºC

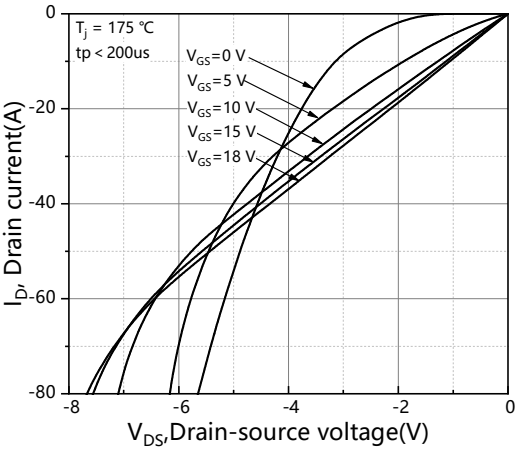


Figure 12. 3rd quadrant characteristic at T_j = 175 ºC

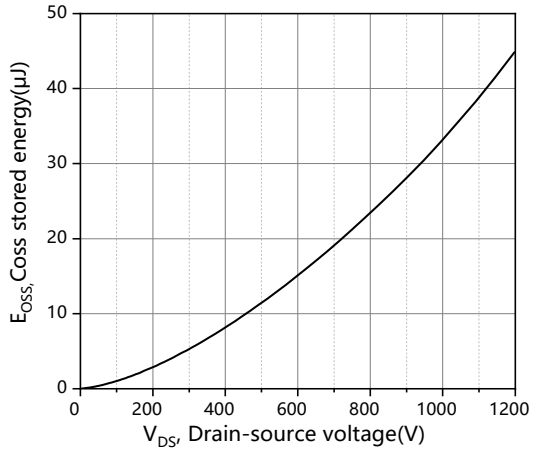


Figure 13. Output capacitor stored energy

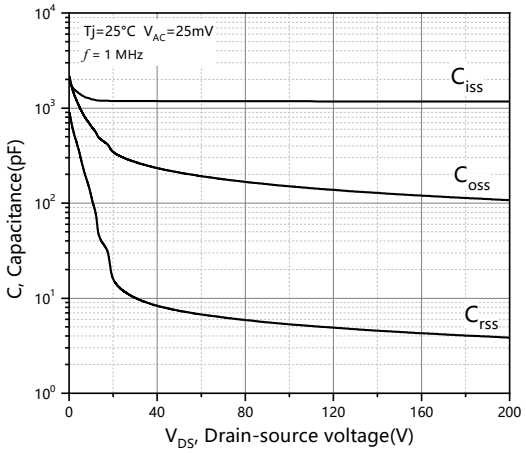


Figure 14. Capacitances vs. drain-source voltage (0 - 200V)

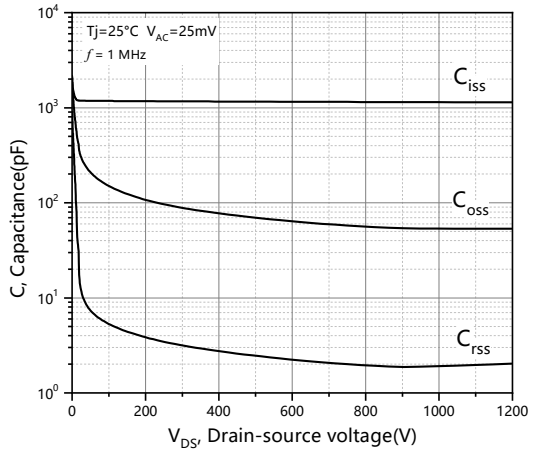


Figure 15. Capacitances vs. drain-source voltage (0 - 1200V)

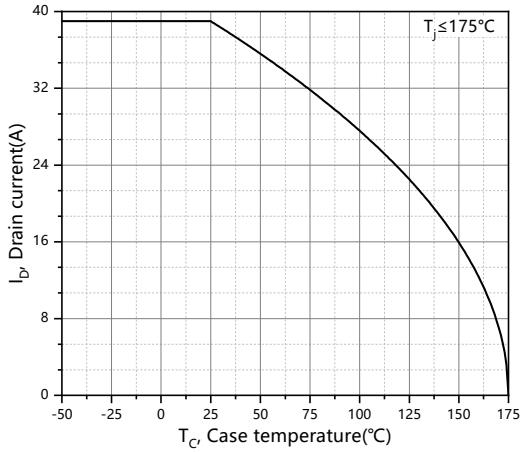


Figure 16. Continuous drain current derating vs.case temperature

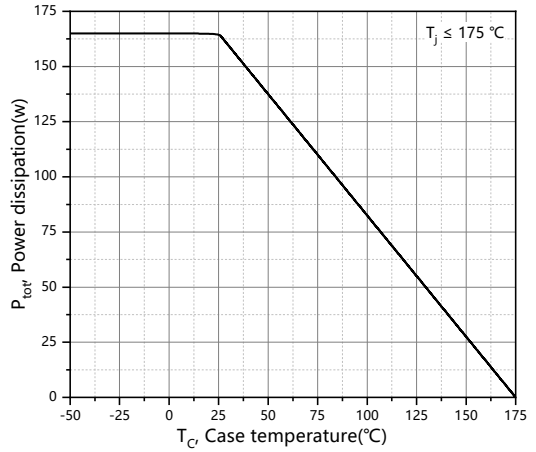


Figure 17. Maximum power dissipation derating vs.case temperature

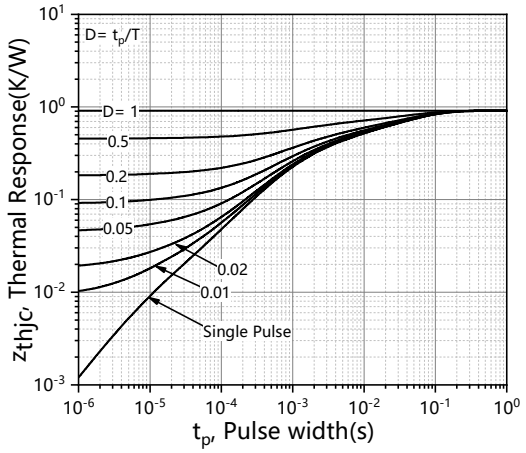


Figure 18. Transient thermal impedance (junction - case)

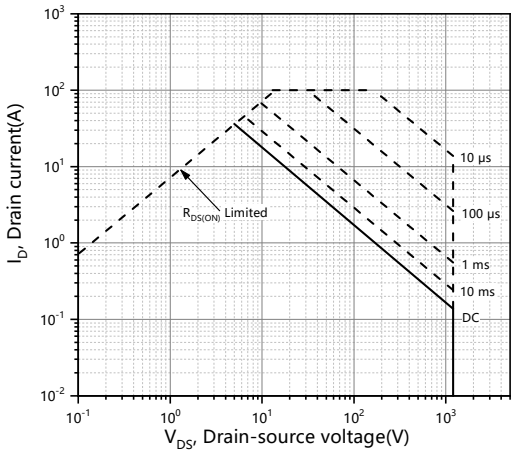


Figure 19. Safe operating area

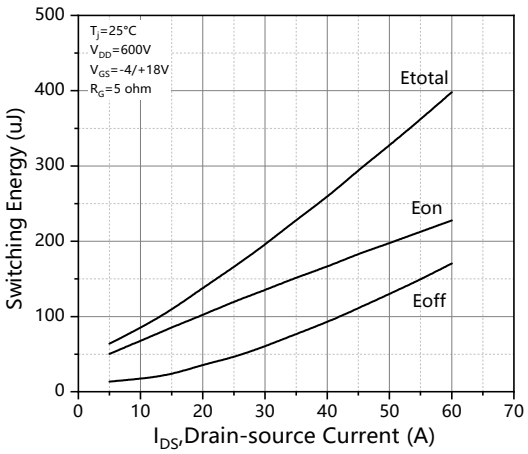


Figure 20. Clamped Inductive switching energy vs.drain current (V_{DD} = 600V)

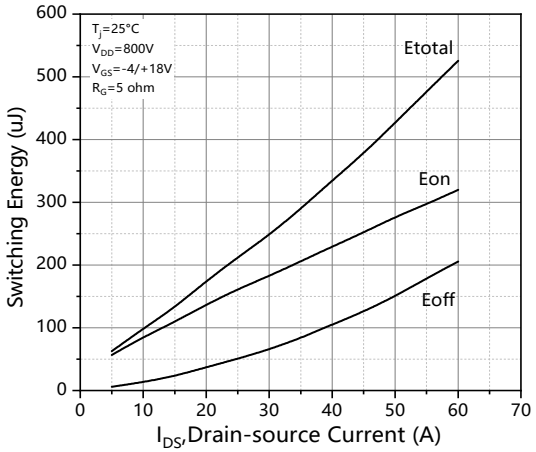


Figure 21. Clamped inductive switching energy vs. drain current (V_{DD} = 800V)

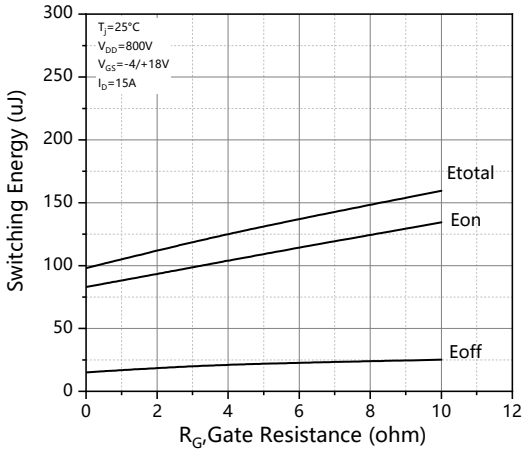


Figure 22. Clamped inductive switching energy vs. R_G

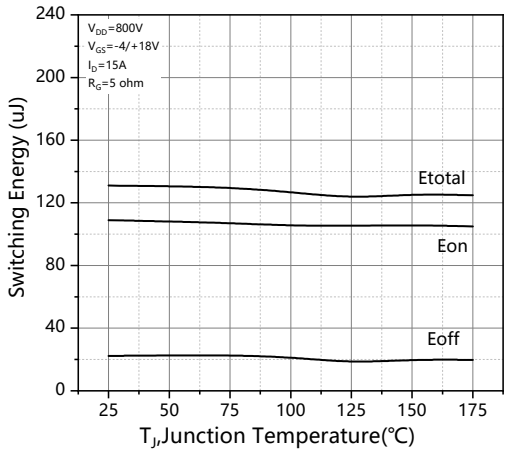


Figure 23. Clamped inductive switching energy vs. temperature

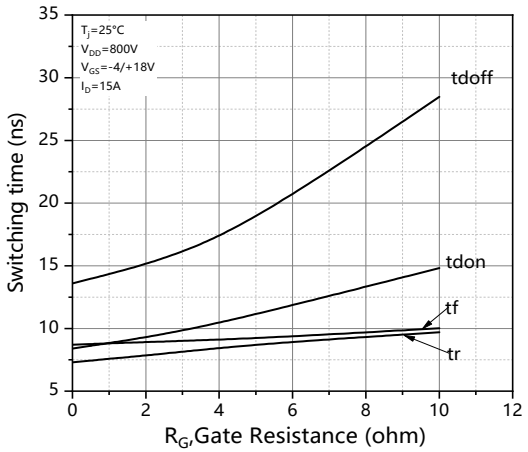
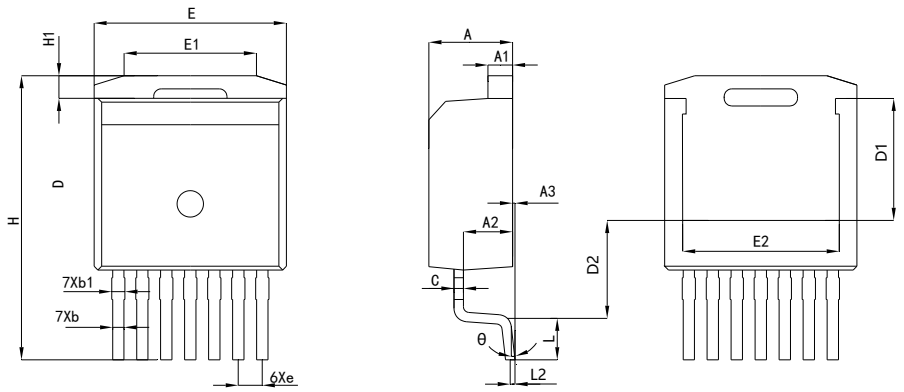


Figure 24. Switching times vs. R_G

Package Information



Symbol	mm		
	Min	Nom	Max
A	4.30	4.43	4.56
A1	1.20	1.30	1.40
A2	2.45	2.60	2.75
A3	0.00	0.13	0.25
b	0.50	0.60	0.70
b1	0.60	0.70	0.90
c	0.45	0.50	0.60
D	8.93	9.08	9.23
D1	6.30	6.45	6.60
D2	5.18 REF		
e	1.27 BSC		
E	10.08	10.18	10.28
E1	7.00 REF		
E2	7.90	8.30	8.70
H	14.53	15.03	15.53
H1	0.98	1.20	1.42
L	1.90	2.20	2.50
L2	0.25 BSC		
θ	0°	3°	7°

Version：TO263-7L-P package outline dimension

Ordering Information

Package Type	Units/ Reel	Reels/ Inner Box	Units/ Inner Box	Inner Boxes/ Carton Box	Units/ Carton Box
TO263-7L-P	800	1	800	5	4000

Product Information

Product	Package	Pb Free	RoHS	Halogen Free
OSQ120R060K7T2AF	TO263-7L	yes	yes	yes

Legal Disclaimer

The information given in this document shall in no event be regarded as a guarantee of conditions or characteristics. With respect to any examples or hints given herein, any typical values stated herein and/or any information regarding the application of the device, Oriental Semiconductor hereby disclaims any and all warranties and liabilities of any kind, including without limitation, warranties of non-infringement of intellectual property rights of any third party.

For further information on technology, delivery terms and conditions and prices, please contact the Oriental Semiconductor sales representatives (www.orientalsemi.com).

Revision History

Version	Revision History	Date
V1.0	Initial release	2026-01-14

ORIENTAL SEMICONDUCTOR

A Power Semiconductor Innovator